3.3 V LVTTL/LVCMOS to **Differential LVECL Translator**

Description

The MC100EPT24 is a LVTTL/LVCMOS to differential LVECL translator. Because LVECL levels and LVTTL/LVCMOS levels are used, a -3.3 V, +3.3 V and ground are required. The small outline 8-lead package and the single gate of the EPT24 makes it ideal for those applications where space, performance, and low power are at a premium.

Features

- 350 ps Typical Propagation Delay
- Maximum Input Clock Frequency = > 1.0 GHz Typical
- The 100 Series Contains Temperature Compensation
- Operating Range:

 V_{CC} = 3.0 V to 3.6 V; V_{EE} = -3.6 V to -3.0 V; GND = 0 V

- PNP LVTTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



ON Semiconductor®

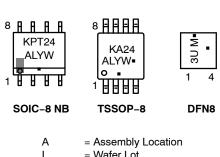
www.onsemi.com



SOIC-8 NB TSSOP-8 DENS DT SUFFIX D SUFFIX CASE 751-07 CASE 948R-02 CASE 506AA

MARKING DIAGRAMS*





L	= Wafer Lot
Υ	= Year
W	= Work Week
Μ	= Date Code
	= Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
MC100EPT24DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EPT24DR2G	SOIC-8 NB (Pb-Free)	2500 Tape & Reel
MC100EPT24DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EPT24MNR4G	DFN8 (Pb-Free)	1000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

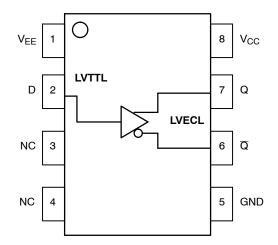


Table 1. PIN DESCRIPTION

PIN	FUNCTION
Q, <u>Q</u>	Differential LVECL Outputs
D	LVTTL Input
V _{CC}	Positive Supply
GND	Ground
V _{EE}	Negative Supply
NC	No Connect
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient ther- mal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	181 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

Table 2. ATTRIBUTES

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Positive Power Supply	GND = 0 V	V _{EE} = -3.3V	3.8	V
V_{EE}	Negative Power Supply	GND = 0 V	V _{CC} = 3.3V	-3.8	V
V _{IN}	Input Voltage	GND = 0 V	$V_{I} \leq V_{CC}$	0 to V _{CC}	V
l _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	SOIC-8 NB SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	DFN8 DFN8	129 84	°C/W
T _{sol}	Wave Solder (Pb-Free)			265	°C
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
I _{IH}	Input HIGH Current	V _{IN} = 2.7 V			20	μΑ
I _{IHH}	Input HIGH Current HIGH Voltage	$V_{CC} = V_{IN} = 3.8 V$			100	μΑ
IIL	Input LOW Current	V _{IN} = 0.5 V			-0.6	mA
V _{IK}	Input Clamp Voltage	I _{IN} = -18 mA			-1.0	V
VIH	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage				0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 5. NECL OUTPUT DC CHARACTERISTICS (V_{CC} = 3.3 V, V_{EE} = -3.3 V, GND = 0.0 V (Note 1))

		-40°C		25°C							
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1030	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
I _{CC}	Positive Power Supply Current		2.0	4.0		2.0	4.0		2.0	4.0	mA
I _{EE}	Negative Power Supply Current	20	30	38	20	30	38	20	30	38	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Output levels will vary 1:1 with GND. V_{EE} can vary \pm 0.3 V.

2. Outputs are terminated through a 50 Ω resistor to GND – 2 V.

		-40°C			25°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Input Clock Frequency (Figure 2)		> 1			> 1			> 1		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential (Note 2)		500	800	300	530	800	300	560	800	ps
t _{JITTER}	RMS Random Clock Jitter (Figure 2)		0.2	< 1		0.2	< 1		0.2	< 1	ps
t _r t _f	Output Rise/Fall Times Q, Q (20% - 80%) @ 50 MHz	70	125	170	80	130	180	100	150	200	ps

Table 6. AC CHARACTERISTICS ($V_{CC} = 0 V$; $V_{EE} = -3.0 V$ to -5.5 V or $V_{CC} = 3.0 V$ to 5.5 V; $V_{EE} = 0 V$ (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured using a LVTTL source, 50% duty cycle clock source. All loading with 50 Ω to GND – 2.0 V.

2. Specifications for standard TTL input signal.

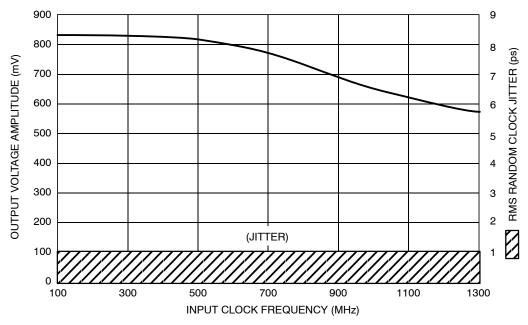


Figure 2. Output Voltage Amplitude (V_{OUTpp})/RMS Jitter vs. Input Clock Frequency at Ambient Temperature

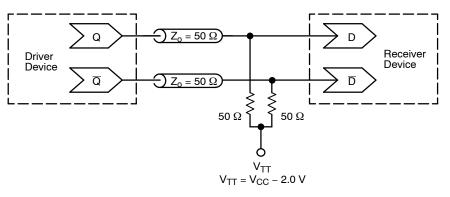


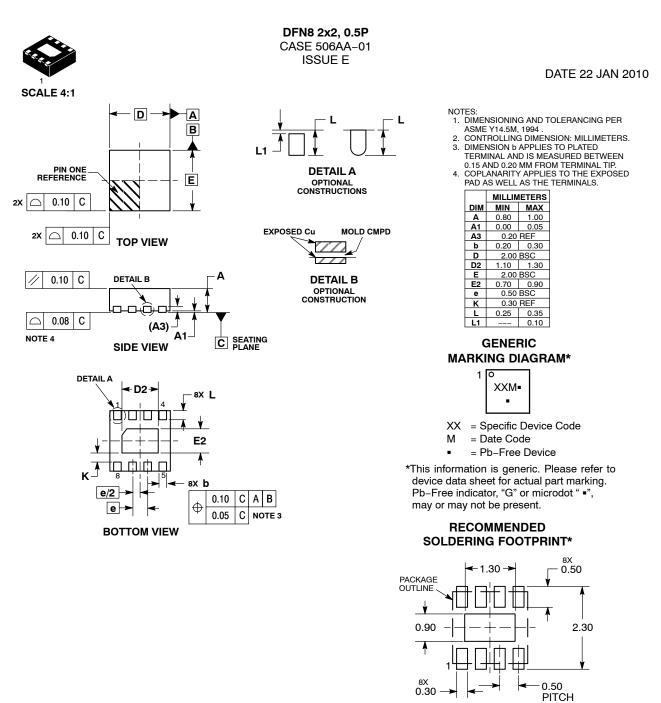
Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices)

Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques
AN1406/D	-	Designing with PECL (ECL at +5.0 V)
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit
AN1504/D	-	Metastability and the ECLinPS Family
AN1568/D	-	Interfacing Between LVDS and ECL
AN1672/D	-	The ECL Translator Guide
AND8001/D	-	Odd Number Counters Design
AND8002/D	-	Marking and Date Codes
AND8020/D	-	Termination of ECL Logic Devices
AND8066/D	-	Interfacing with ECLinPS
AND8090/D	-	AC Characteristics of ECL Devices

ECLinPS is a trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.





DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITC	PITCH PAGE 1 OF					
ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights or the							





*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repose Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2				
ON Semiconductor reserves the right the suitability of its products for any pa	to make changes without further notice to an articular purpose, nor does ON Semiconducto	stries, LLC dba ON Semiconductor or its subsidiaries in the United States y products herein. ON Semiconductor makes no warranty, representation r assume any liability arising out of the application or use of any product on hcidental damages. ON Semiconductor does not convey any license under	or guarantee regarding r circuit, and specifically				

SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: CATHODE 1 PIN 1. 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC COMMON CATHODE/VCC 3 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2	
ON Semiconductor and unarrest and the trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the				

SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

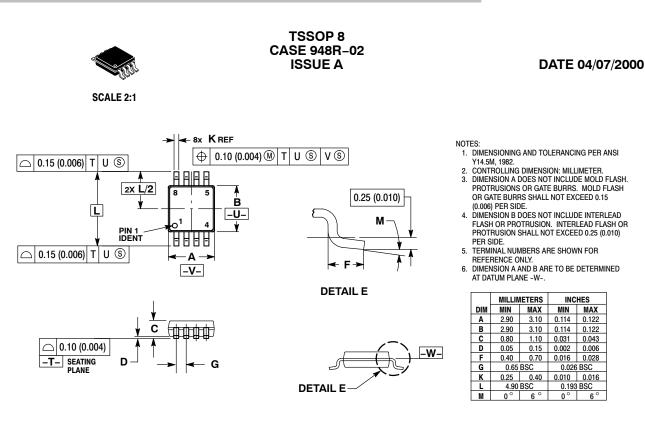
8

rights of others

COLLECTOR, #1

COLLECTOR, #1





DOCUMENT NUMBER:	98AON00236D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP 8		PAGE 1 OF 1	
ON Semiconductor and (1) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the				

[©] Semiconductor Components Industries, LLC, 2019

rights of others.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor date sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use a a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor houteds for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative